

3. the greater the positive difference between  $(E_g/2 + \chi - \Phi_m)$  and work function  $\Phi_m$  the greater charge exchange occurs to achieve equilibrium, filling some bulk traps as well; and."

#### REMARKS

The above amendments are made to correct some typographical errors in the specification. No new matter is added. Early and favorable action in connection with this application is respectfully requested.

Respectfully submitted,



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## APPENDIX

### IN THE SPECIFICATION:

1. When contact is made between an n-type semiconductor and a conductor whose work function  $\Phi_m$  is less than half of  $[(E_g/2 - \chi)]$   $(E_g/2 - \chi)$  where  $E_g$  is the semiconductor band gap and  $\chi$  is the electron affinity, then charge exchange occurs to obtain equilibrium;

3. the greater the positive difference between  $[(E_g/2 - \Phi_m)]$   $(E_g/2 + \chi - \Phi_m)$  and work function  $\Phi_m$  the greater charge exchange occurs to achieve equilibrium, filling some bulk traps as well; and.”.